

Publication list

Journal :

- [1] 楊宗熿、沈詩國、辜瑞泰、張哲榮、陳怡誠、張俊彥，” 分子束磊晶成長氮化鎵在 (111) 矽基板上” ，accepted by 電子月刊

International conference :

- [1] Tsung Hsi Yang, Jet-Chung Chang, Jui Tai Ku, Shih-Guo Shen, Yi-Cheng Chen and Chun-Yen Chang, “Growth of GaN on Si (111) using simultaneous AlN/ α -Si₃N₄ buffer structure”, accepted by 2007 *Solid State Devices and Materials (SSDM)*, Ibaraki, Japan.
- [2] Jet-Chung Chang, Tsung Hsi Yang, Shih-Guo Shen, Chen Yi-Cheng, Jui Tai Ku and Chun-Yen Chang, “The elimination of inversion domains in MBE-GaN grown using low temperature nitridation”, accepted by 2007 *Solid State Devices and Materials (SSDM)*, Ibaraki, Japan.

Patent :

- [1] 張俊彥、楊宗熿、沈詩國，高品質三族氮化物半導體成長在矽基板上的方法，中華民國專利申請中
- [2] 張俊彥，楊宗熿，張哲榮，辜瑞泰，沈詩國，陳怡誠，在矽基板上成長高品質三族氮化物半導體磊晶層的方法，中華民國專利申請中

